



STF2907A

SMALL SIGNAL PNP TRANSISTOR

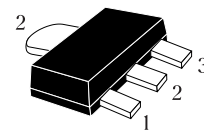
PRELIMINARY DATA

Type	Marking
STF2907A	03F

- SILICON EPITAXIAL PLANAR PNP TRANSISTOR
- MINIATURE SOT-89 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE & REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS STF2222A

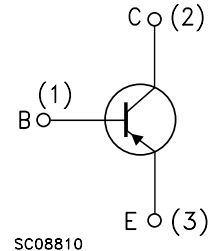
APPLICATIONS

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE



SOT-89

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Emitter Voltage ($I_E = 0$)	-60	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-60	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_{CM}	Collector Peak Current	-0.8	A
P_{tot}	Total Dissipation at $T_C = 25\text{ }^\circ\text{C}$	1.2	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

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THERMAL DATA

$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	104.1	$^{\circ}\text{C}/\text{W}$
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• Device mounted on a PCB area of 1 cm^2

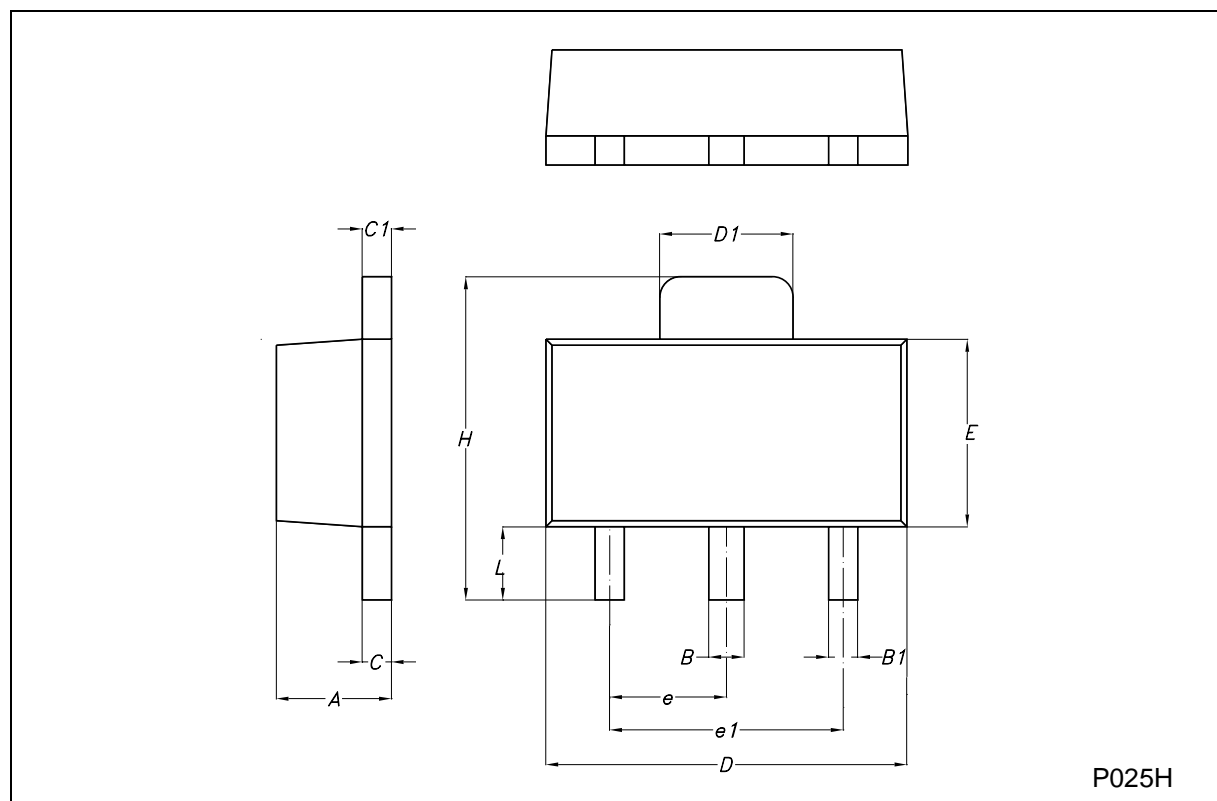
ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEX}	Collector Cut-off Current ($V_{BE} = -3\text{ V}$)	$V_{CE} = -30\text{ V}$			-50	nA
I_{BEX}	Base Cut-off Current ($V_{BE} = -3\text{ V}$)	$V_{CE} = -30\text{ V}$			-50	nA
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = -50\text{ V}$			-10	nA
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = -10\text{ mA}$	-60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = -10\text{ }\mu\text{A}$	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = -10\text{ }\mu\text{A}$	-5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -150\text{ mA}$ $I_B = -15\text{ mA}$ $I_C = -500\text{ mA}$ $I_B = -50\text{ mA}$			-0.4 -1.6	V V
$V_{BE(sat)}^*$	Collector-Base Saturation Voltage	$I_C = -150\text{ mA}$ $I_B = -15\text{ mA}$ $I_C = -500\text{ mA}$ $I_B = -50\text{ mA}$			-1.3 -2.6	V V
h_{FE}^*	DC Current Gain	$I_C = -0.1\text{ mA}$ $V_{CE} = -10\text{ V}$ $I_C = -1\text{ mA}$ $V_{CE} = -10\text{ V}$ $I_C = -10\text{ mA}$ $V_{CE} = -10\text{ V}$ $I_C = -150\text{ mA}$ $V_{CE} = -10\text{ V}$ $I_C = -500\text{ mA}$ $V_{CE} = -10\text{ V}$	75 100 100 100 50		300	
f_T	Transition Frequency	$I_C = -50\text{ mA}$ $V_{CE} = -20\text{ V}$ $f = 100\text{ MHz}$	200			MHz
C_{CBO}	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = -10\text{ V}$ $f = 1\text{ MHz}$			8	pF
C_{EBO}	Emitter-Base Capacitance	$I_C = 0$ $V_{EB} = -2\text{ V}$ $f = 1\text{ MHz}$			30	pF
t_d	Delay Time	$I_C = -150\text{ mA}$ $I_B = -15\text{ mA}$ $V_{CC} = -30\text{ V}$			10	ns
t_r	Rise Time				40	ns
t_{on}	Switching On Time				45	ns
t_s	Storage Time	$I_C = -150\text{ mA}$ $I_{B1} = -I_{B2} = -15\text{ mA}$ $V_{CC} = -30\text{ V}$		190		ns
t_f	Fall Time				30	ns
t_{off}	Switching Off Time			220		ns

* Pulsed: Pulse duration = $300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

SOT-89 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.4		1.6	55.1		63.0
B	0.44		0.56	17.3		22.0
B1	0.36		0.48	14.2		18.9
C	0.35		0.44	13.8		17.3
C1	0.35		0.44	13.8		17.3
D	4.4		4.6	173.2		181.1
D1	1.62		1.83	63.8		72.0
E	2.29		2.6	90.2		102.4
e	1.42		1.57	55.9		61.8
e1	2.92		3.07	115.0		120.9
H	3.94		4.25	155.1		167.3
L	0.89		1.2	35.0		47.2



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